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# **Phase-Locked Loop**

## High-Performance Silicon-Gate CMOS

The MC74HC4046B is similar in function to the MC14046 Metal gate CMOS device. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC4046B phase-locked loop contains three phase comparators, a voltage-controlled oscillator (VCO) and unity gain op-amp DEM<sub>OUT</sub>. The comparators have two common signal inputs, COMPIN, and SIGIN. Input SIGIN and COMPIN can be used directly coupled to large voltage signals, or indirectly coupled (with a series capacitor to small voltage signals). The self-bias circuit adjusts small voltage signals in the linear region of the amplifier. Phase comparator 1 (an exclusive OR gate) provides a digital error signal PC1<sub>OUT</sub> and maintains 90 degrees phase shift at the center frequency between SIG<sub>IN</sub> and COMP<sub>IN</sub> signals (both at 50% duty cycle). Phase comparator 2 (with leading-edge sensing logic) provides digital error signals PC2<sub>OUT</sub> and PCP<sub>OUT</sub> and maintains a 0 degree phase shift between SIG<sub>IN</sub> and COMP<sub>IN</sub> signals (duty cycle is immaterial). The linear VCO produces an output signal VCO<sub>OUT</sub> whose frequency is determined by the voltage of input VCO<sub>IN</sub> signal and the capacitor and resistors connected to pins C1A, C1B, R1 and R2. The unity gain op-amp output DEMOUT with an external resistor is used where the VCO<sub>IN</sub> signal is needed but no loading can be tolerated. The inhibit input, when high, disables the VCO and all op-amps to minimize standby power consumption.

Applications include FM and FSK modulation and demodulation, frequency synthesis and multiplication, frequency discrimination, tone decoding, data synchronization and conditioning, voltage-tofrequency conversion and motor speed control.

#### Features

- Output Drive Capability: 10 LSTTL Loads
- Low Power Consumption Characteristic of CMOS Devices
- Operating Speeds Similar to LSTTL
- Wide Operating Voltage Range for VCO: 3.0 to 6.0 V
- Low Input Current: 1.0 µA Maximum (except SIG<sub>IN</sub> and COMP<sub>IN</sub>)
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Low Quiescent Current: 80 μA Maximum (VCO disabled)
- High Noise Immunity Characteristic of CMOS Devices
- Diode Protection on All Inputs
- Chip Complexity: 279 FETs or 70 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free and are RoHS Compliant



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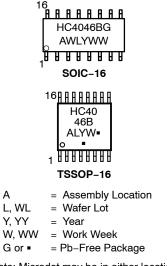


TSSOP-16 DT SUFFIX CASE 948F

### **PIN ASSIGNMENT**

			_
PCP <sub>out</sub>	1●		] v <sub>cc</sub>
PC1 <sub>out</sub>	2	15	] PC3 <sub>out</sub>
COMP <sub>in</sub>	3	14	] SIG <sub>in</sub>
VCO <sub>out</sub> [	4	13	] PC2 <sub>out</sub>
INH [	5	12	] R2
C1A	6	11	] R1
С1В [	7	10	DEM <sub>out</sub>
gnd [	8	9	] vco <sub>in</sub>

#### MARKING DIAGRAMS



(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 11 of this data sheet

Pin No.	Symbol	Name and Function
1	PCPOUT	Phase Comparator Pulse Output
2	PC1 <sub>OUT</sub>	Phase Comparator 1 Output
3	COMPIN	Comparator Input
4	VCO <sub>OUT</sub>	VCO Output
5	INH	Inhibit Input
6	C1A	Capacitor C1 Connection A
7	C1B	Capacitor C1 Connection B
8	GND	Ground (0 V) V <sub>SS</sub>
9	VCOIN	VCO Input
10	DEMOUT	Demodulator Output
11	R1	Resistor R1 Connection
12	R2	Resistor R2 Connection
13	PC2 <sub>OUT</sub>	Phase Comparator 2 Output
14	SIG <sub>IN</sub>	Signal Input
15	PC3 <sub>OUT</sub>	Phase Comparator 3 Output
16	V <sub>CC</sub>	Positive Supply Voltage

#### MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	-1.5 to V <sub>CC</sub> + 1.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	–0.5 to V <sub>CC</sub> + 0.5	V
l <sub>in</sub>	DC Input Current, per Pin	±20	mA
l <sub>out</sub>	DC Output Current, per Pin	±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±50	mA
PD	Power Dissipation in Still Air SOIC Package†	500	mW
T <sub>stg</sub>	Storage Temperature	–65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds SOIC Package†	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Min	Мах	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)		3.0	6.0	V
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND) NON-VCO		2.0	6.0	V
$V_{in}, V_{out}$	DC Input Voltage, Output Voltage (Referenced to GND)		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $V_{CC} =$ (Pin 5) $V_{CC} =$ $V_{CC} =$	4.5 V	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## [Phase Comparator Section] DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			Vcc	Guar	anteed Lin	nit	
Symbol	Parameter	Test Conditions	V	–55 to 25°C	≤ <b>85°C</b>	≤ 125°C	Unit
VIH	Minimum High–Level Input Voltage DC Coupled SIG <sub>IN</sub> , COMP <sub>IN</sub>	$\begin{array}{l} V_{out} = 0.1 \ V \ or \ V_{CC} - 0.1 \ V \\  I_{out}  \leq 20 \ \mu A \end{array}$	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage DC Coupled SIG <sub>IN</sub> , COMP <sub>IN</sub>	$\begin{array}{l} V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V} \\  I_{out}  \leq 20 \ \mu\text{A} \end{array}$	2.0 4.5 6.0	0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage PCP <sub>OUT</sub> , PCn <sub>OUT</sub>	$ \begin{array}{l} V_{in} = V_{IH} \text{ or } V_{IL} \\  I_{out}  \leq 20 \ \mu A \end{array} $	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{array}{l} V_{in} = V_{IH} \text{ or } V_{IL} \\  I_{out}  \leq 4.0 \text{ mA} \\  I_{out}  \leq 5.2 \text{ mA} \end{array} $	4.5 6.0	3.98 5.48	3.84 5.34	3.7 5.2	
V <sub>OL</sub>	Maximum Low-Level Output Voltage Qa-Qh PCP <sub>OUT</sub> , PCn <sub>OUT</sub>	$\begin{array}{l} V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V} \\  I_{out}  \leq 20 \ \mu\text{A} \end{array}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$ \begin{array}{l} V_{in} = V_{IH} \text{ or } V_{IL} \\  I_{out}  \leq 4.0 \text{ mA} \\  I_{out}  \leq 5.2 \text{ mA} \end{array} $	4.5 6.0	0.26 0.3	0.33 0.34	0.4 0.4	
l <sub>in</sub>	Maximum Input Leakage Current SIG <sub>IN</sub> , COMP <sub>IN</sub>	$V_{in} = V_{CC}$ or GND	2.0 3.0 4.5 6.0	±3.0 ±8.5 ±24 ±108	±4.0 ±9.0 ±24 ±108	±5.0 ±11.0 ±27.0 ±108	μA
I <sub>OZ</sub>	Maximum Three-State Leakage Current PC2 <sub>OUT</sub>	$\begin{array}{l} \text{Output in High-Impedance State} \\ \text{V}_{in} = \text{V}_{IH} \text{ or } \text{V}_{IL} \\ \text{V}_{out} = \text{V}_{CC} \text{ or GND} \end{array}$	6.0	±0.5	±5.0	±10	μΑ
Icc	Maximum Quiescent Supply Current (per Package) (VCO disabled) Pins 3, 5 and 14 at V <sub>CC</sub> Pin 9 at GND; Input Leakage at Pins 3 and 14 to be excluded	V <sub>in</sub> = V <sub>CC</sub> or GND  I <sub>out</sub>   = 0 μA	6.0	160	160	160	μA

## [Phase Comparator Section]

AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6.0 \text{ ns}$ )

		V <sub>cc</sub>	Guar	anteed Lim	nit	
Symbol	Parameter	v	–55 to 25°C	≤ 85°C	≤ 125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, SIG <sub>IN</sub> /COMP <sub>IN</sub> to PC1 <sub>OUT</sub> (Figure 1)	2.0 4.5 6.0	175 35 30	220 44 37	265 53 45	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, SIG <sub>IN</sub> /COMP <sub>IN</sub> to PCP <sub>OUT</sub> (Figure 1)	2.0 4.5 6.0	340 68 58	425 85 72	510 102 87	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, SIG <sub>IN</sub> /COMP <sub>IN</sub> to PC3 <sub>OUT</sub> (Figure 1)	2.0 4.5 6.0	270 54 46	340 68 58	405 81 69	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, SIG <sub>IN</sub> /COMP <sub>IN</sub> Output Disable Time to PC2 <sub>OUT</sub> (Figures 2 and 3)	2.0 4.5 6.0	200 40 34	250 50 43	300 60 51	ns
t <sub>PZH</sub> , t <sub>PZL</sub>	Maximum Propagation Delay, SIG <sub>IN</sub> /COMP <sub>IN</sub> Output Enable Time to PC2 <sub>OUT</sub> (Figures 2 and 3)	2.0 4.5 6.0	230 46 39	290 58 49	345 69 59	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time (Figure 1)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns

## [VCO Section] DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

		v	Vcc	Guaranteed Limit						
Symbol	Parameter	Test Conditions	V	–55 to	o 25°C	≤ <b>8</b>	5°C	≤ 12	25°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage INH	$\label{eq:Vout} \begin{split} V_{out} &= 0.1 \text{ V or } V_{CC} - 0.1 \text{ V} \\ \left I_{out}\right  &\leq 20 \ \mu\text{A} \end{split}$	3.0 4.5 6.0	3.	.1 15 .2	3.	.1 15 .2	3.	.1 15 .2	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage INH	$\label{eq:Vout} \begin{split} V_{out} &= 0.1 \text{ V or } V_{CC} - 0.1 \text{ V} \\  I_{out}  &\leq 20 \ \mu\text{A} \end{split}$	3.0 4.5 6.0	1.	90 35 .8	1.3	.9 35 .8	1.	.9 35 .8	V
V <sub>OH</sub>	Minimum High–Level Output Voltage VCO <sub>OUT</sub>		3.0 4.5 6.0	4	.9 .4 .9	4	.9 .4 .9	4	.9 .4 .9	V
		$ \begin{aligned} & V_{in} = V_{IH} \text{ or } V_{IL} \\ &  I_{out}  \leq 4.0 \text{ mA} \\ &  I_{out}  \leq 5.2 \text{ mA} \end{aligned} $	4.5 6.0	5.	98 48	5.	84 34	5	.7 .2	
V <sub>OL</sub>	Maximum Low-Level Output Voltage VCO <sub>OUT</sub>	$\label{eq:Vout} \begin{split} V_{out} &= 0.1 \text{ V or } V_{CC} - 0.1 \text{ V} \\ \left I_{out}\right  &\leq 20 \ \mu\text{A} \end{split}$	3.0 4.5 6.0	0	.1 .1 .1	0 0 0	.1	0	.1 .1 .1	V
		$ \begin{aligned} &V_{in} = V_{IH} \text{ or } V_{IL} \\ & I_{out}  \leq 4.0 \text{ mA} \\ & I_{out}  \leq 5.2 \text{ mA} \end{aligned} $	4.5 6.0		26 .3		33 34		.4 .4	
l <sub>in</sub>	Maximum Input Leakage Current INH, VCO <sub>IN</sub>	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	0	.1	1	.0	1	.0	μA
				Min	Max	Min	Max	Min	Max	
V <sub>VCO</sub> IN	Operating Voltage Range at VCO <sub>IN</sub> over the range specified for R1; For linearity see Fig. 13A, Parallel value of R1 and R2 should be > $2.7 \text{ k}\Omega$	INH = V <sub>IL</sub>	3.0 4.5 6.0	0.1 0.1 0.1	1.0 2.5 4.0	0.1 0.1 0.1	1.0 2.5 4.0	0.1 0.1 0.1	1.0 2.5 4.0	V
R1	Resistor Range		3.0 4.5 6.0	3.0 3.0 3.0	300 300 300	3.0 3.0 3.0	300 300 300	3.0 3.0 3.0	300 300 300	kΩ
R2			3.0 4.5 6.0	3.0 3.0 3.0	300 300 300	3.0 3.0 3.0	300 300 300	3.0 3.0 3.0	300 300 300	
C1	Capacitor Range		3.0 4.5 6.0	40 40 40	No Limit					pF

## [VCO Section]

```
AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns)
```

				G	uarant	eed Lin	nit		
		v <sub>cc</sub>	–55 to	o 25°C	≤ <b>8</b>	5°C	≤ <b>1</b> 2	25°C	
Symbol	Parameter	v	Min	Max	Min	Max	Min	Max	Unit
$\Delta f/T$	Frequency Stability with Temperature Changes (Figures 11A, B, C)	3.0 4.5 6.0							%/K
fo	VCO Center Frequency (Duty Factor = 50%, R1 = 3 k $\Omega$ , C1 = 39 pF, R2 = infinity) (See Figures 12A, B, C, D for other conditions)	3.0 4.5 6.0	3 11 13						MHz
∆fVCO	VCO Frequency Linearity	3.0 4.5 6.0	See Figures 13A, B				%		
9 ACO	Duty Factor at VCO <sub>OUT</sub>	3.0 4.5 6.0			Туріса	al 50%			%

## [Demodulator Section] DC ELECTRICAL CHARACTERISTICS

					G	uarante	eed Lin	nit		
			v <sub>cc</sub>	-55 to	o 25°C	≤ <b>8</b>	5°C	≤ 12	25°C	
Symbol	Parameter	Test Conditions	V	Min	Max	Min	Max	Min	Max	Unit
RS	Resistor Range	At RS > 300 kΩ the Leakage Current can Influence VDEM <sub>OUT</sub>	3.0 4.5 6.0	50 50 50	300 300 300					kΩ
V <sub>OFF</sub>	Offset Voltage VCO <sub>IN</sub> to VDEM <sub>OUT</sub>	Vi = VVCO <sub>IN</sub> = 1/2 V <sub>CC</sub> ; Values taken over RS Range.	3.0 4.5 6.0	See Figure 10					mV	
RD	Dynamic Output Resistance at DEM <sub>OUT</sub>	VDEM <sub>OUT</sub> = 1/2 V <sub>CC</sub>	3.0 4.5 6.0			Туріса	al 25 Ω			Ω

## SWITCHING WAVEFORMS

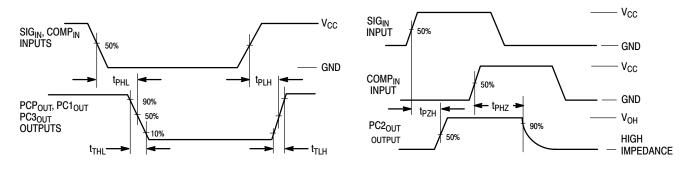
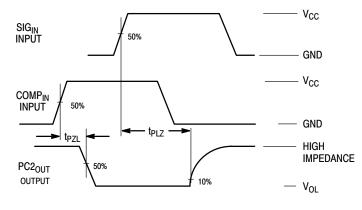
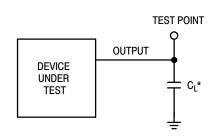


Figure 1.

Figure 2.







\*INCLUDES ALL PROBE AND JIG CAPACITANCE



#### DETAILED CIRCUIT DESCRIPTION

#### Voltage Controlled Oscillator/Demodulator Output

The VCO requires two or three external components to operate. These are R1, R2, C1. Resistor R1 and Capacitor C1 are selected to determine the center frequency of the VCO (see typical performance curves Figure 12). R2 can be used to set the offset frequency with 0 volts at VCO input. For example, if R2 is decreased, the offset frequency is increased. If R2 is omitted the VCO range is from 0 Hz. By increasing the value of R2 the lock range of the PLL is increased and the gain (volts/Hz) is decreased. Thus, for a narrow lock range, large swings on the VCO input will cause less frequency variation.

Internally, the resistors set a current in a current mirror, as shown in Figure 5. The mirrored current drives one side of the capacitor. Once the voltage across the capacitor charges up to  $V_{ref}$  of the comparators, the oscillator logic flips the

capacitor which causes the mirror to charge the opposite side of the capacitor. The output from the internal logic is then taken to VCO output (Pin 4).

The input to the VCO is a very high impedance CMOS input and thus will not load down the loop filter, easing the filter design. In order to make signals at the VCO input accessible without degrading the loop performance, the VCO input voltage is buffered through a unity gain Op–amp to Demod Output. This Op–amp can drive loads of 50K ohms or more and provides no loading effects to the VCO input voltage (see Figure 10).

An inhibit input is provided to allow disabling of the VCO and all Op–amps (see Figure 5). This is useful if the internal VCO is not being used. A logic high on inhibit disables the VCO and all Op–amps, minimizing standby power consumption.

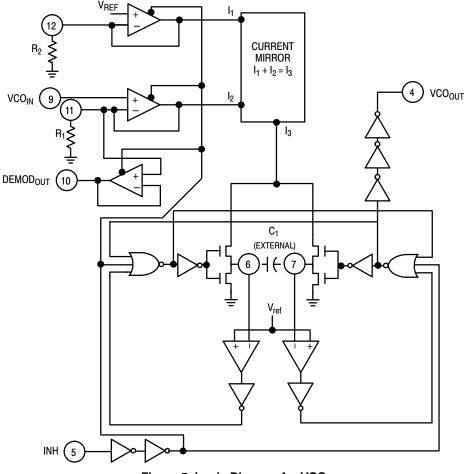


Figure 5. Logic Diagram for VCO

The output of the VCO is a standard high speed CMOS output with an equivalent LS–TTL fan out of 10. The VCO output is approximately a square wave. This output can either directly feed the COMP<sub>IN</sub> of the phase comparators or feed external prescalers (counters) to enable frequency synthesis.

#### **Phase Comparators**

All three phase comparators have two inputs,  $SIG_{IN}$  and  $COMP_{IN}$ . The  $SIG_{IN}$  and  $COMP_{IN}$  have a special DC bias

network that enables AC coupling of input signals. If the signals are not AC coupled, standard 74HC input levels are required. Both input structures are shown in Figure 6. The outputs of these comparators are essentially standard 74HC outputs (comparator 2 is TRI–STATEABLE). In normal operation  $V_{CC}$  and ground voltage levels are fed to the loop filter. This differs from some phase detectors which supply a current to the loop filter and should be considered in the design. (The MC14046 also provides a voltage).

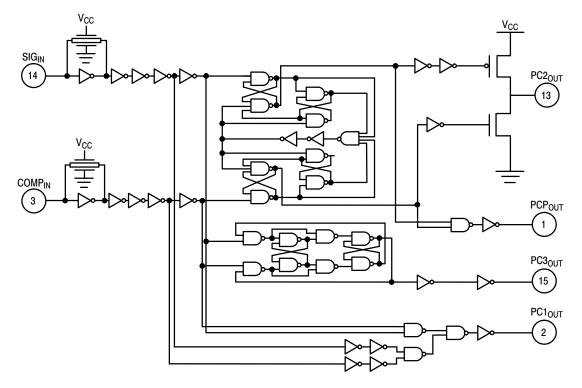
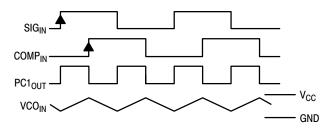


Figure 6. Logic Diagram for Phase Comparators

#### **Phase Comparator 1**

This comparator is a simple XOR gate similar to the 74HC86. Its operation is similar to an overdriven balanced modulator. To maximize lock range the input frequencies must have a 50% duty cycle. Typical input and output waveforms are shown in Figure 7. The output of the phase detector feeds the loop filter which averages the output voltage. The frequency range upon which the PLL will lock onto if initially out of lock is defined as the capture range. The capture range for phase detector 1 is dependent on the loop filter design. The capture range can be as large as the lock range, which is equal to the VCO frequency range.

To see how the detector operates, refer to Figure 7. When two square wave signals are applied to this comparator, an output waveform (whose duty cycle is dependent on the phase difference between the two signals) results. As the phase difference increases, the output duty cycle increases and the voltage after the loop filter increases. In order to achieve lock when the PLL input frequency increases, the VCO input voltage must increase and the phase difference between COMP<sub>IN</sub> and SIG<sub>IN</sub> will increase. At an input frequency equal to  $f_{min}$ , the VCO input is at 0 V. This requires the phase detector output to be grounded; hence, the two input signals must be in phase. When the input frequency is  $f_{max}$ , the VCO input must be  $V_{CC}$  and the phase detector inputs must be 180 degrees out of phase.



#### Figure 7. Typical Waveforms for PLL Using Phase Comparator 1

The XOR is more susceptible to locking onto harmonics of the  $SIG_{IN}$  than the digital phase detector 2. For instance,

a signal 2 times the VCO frequency results in the same output duty cycle as a signal equal to the VCO frequency. The difference is that the output frequency of the 2f example is twice that of the other example. The loop filter and VCO range should be designed to prevent locking on to harmonics.

#### **Phase Comparator 2**

This detector is a digital memory network. It consists of four flip-flops and some gating logic, a three state output and a phase pulse output as shown in Figure 6. This comparator acts only on the positive edges of the input signals and is independent of duty cycle.

Phase comparator 2 operates in such a way as to force the PLL into lock with 0 phase difference between the VCO output and the signal input positive waveform edges. Figure 8 shows some typical loop waveforms. First assume that SIG<sub>IN</sub> is leading the COMP<sub>IN</sub>. This means that the VCO's frequency must be increased to bring its leading edge into proper phase alignment. Thus the phase detector 2 output is set high. This will cause the loop filter to charge up the VCO input, increasing the VCO frequency. Once the leading edge of the COMP<sub>IN</sub> is detected, the output goes TRI–STATE holding the VCO input at the loop filter voltage. If the VCO still lags the SIG<sub>IN</sub> then the phase detector will again charge up the VCO input for the time between the leading edges of both waveforms.

If the VCO leads the SIG<sub>IN</sub> then when the leading edge of the VCO is seen; the output of the phase comparator goes low. This discharges the loop filter until the leading edge of the SIG<sub>IN</sub> is detected at which time the output disables itself again. This has the effect of slowing down the VCO to again make the rising edges of both waveforms coincidental.

When the PLL is out of lock, the VCO will be running either slower or faster than the SIG<sub>IN</sub>. If it is running slower the phase detector will see more SIG<sub>IN</sub> rising edges and so the output of the phase comparator will be high a majority of the time, raising the VCO's frequency. Conversely, if the VCO is running faster than the SIG<sub>IN</sub>, the output of the detector will be low most of the time and the VCO's output frequency will be decreased.

As one can see, when the PLL is locked, the output of phase comparator 2 will be disabled except for minor corrections at the leading edge of the waveforms. When  $PC_2$  is TRI–STATED, the PCP output is high. This output can be used to determine when the PLL is in the locked condition.

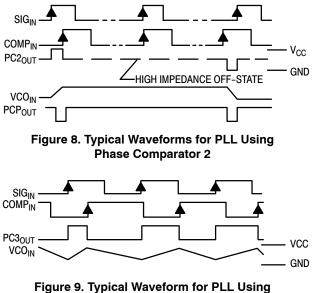
This detector has several interesting characteristics. Over the entire VCO frequency range there is no phase difference between the COMP<sub>IN</sub> and the SIG<sub>IN</sub>. The lock range of the PLL is the same as the capture range. Minimal power was consumed in the loop filter since in lock the detector output is a high impedance. When no SIG<sub>IN</sub> is present, the detector will see only VCO leading edges, so the comparator output will stay low, forcing the VCO to  $f_{min}$ .

Phase comparator 2 is more susceptible to noise, causing the PLL to unlock. If a noise pulse is seen on the SIG<sub>IN</sub>, the comparator treats it as another positive edge of the SIG<sub>IN</sub> and will cause the output to go high until the VCO leading edge is seen, potentially for an entire SIG<sub>IN</sub> period. This would cause the VCO to speed up during that time. When using PC<sub>1</sub>, the output of that phase detector would be disturbed for only the short duration of the noise spike and would cause less upset.

#### Phase Comparator 3

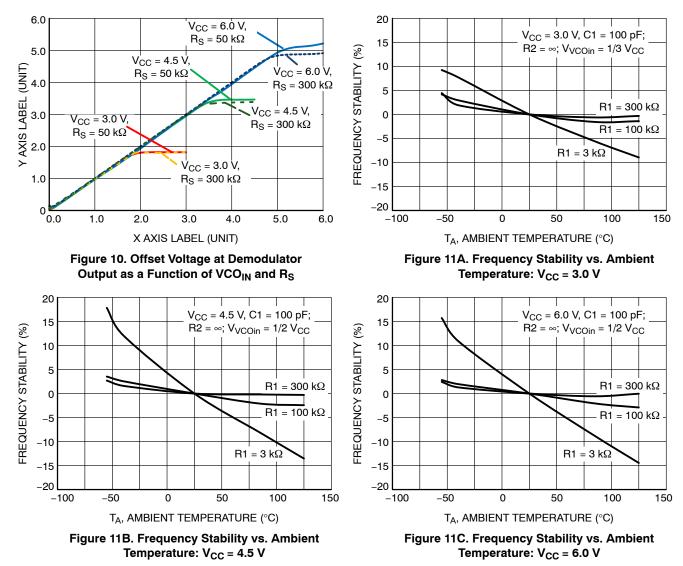
This is a positive edge-triggered sequential phase detector using an RS flip-flop as shown in Figure 6. When the PLL is using this comparator, the loop is controlled by positive signal transitions and the duty factors of SIG<sub>IN</sub> and COMPIN are not important. It has some similar characteristics to the edge sensitive comparator. To see how this detector works, assume input pulses are applied to the SIG<sub>IN</sub> and COMP<sub>IN</sub>'s as shown in Figure 9. When the SIG<sub>IN</sub> leads the COMP<sub>IN</sub>, the flop is set. This will charge the loop filter and cause the VCO to speed up, bringing the comparator into phase with the SIG<sub>IN</sub>. The phase angle between SIG<sub>IN</sub> and COMP<sub>IN</sub> varies from 0° to 360° and is  $180^{\circ}$  at f<sub>o</sub>. The voltage swing for PC<sub>3</sub> is greater than for PC<sub>2</sub> but consequently has more ripple in the signal to the VCO. When no SIG<sub>IN</sub> is present the VCO will be forced to fmax as opposed to  $f_{min}$  when PC<sub>2</sub> is used.

The operating characteristics of all three phase comparators should be compared to the requirements of the system design and the appropriate one should be used.

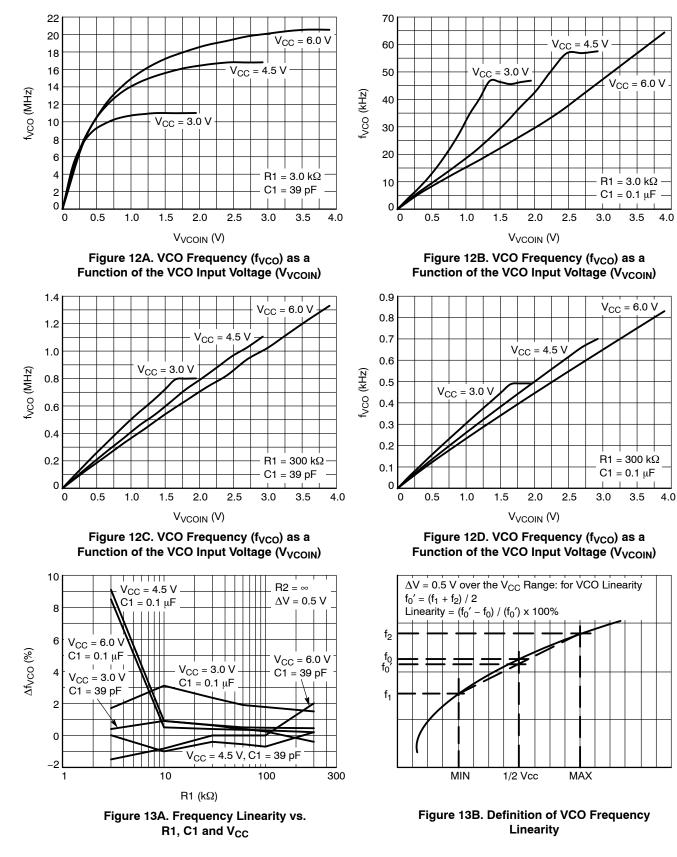


Phase Comparator 3

## **TYPICAL CHARACTERISTICS**



## **TYPICAL CHARACTERISTICS**



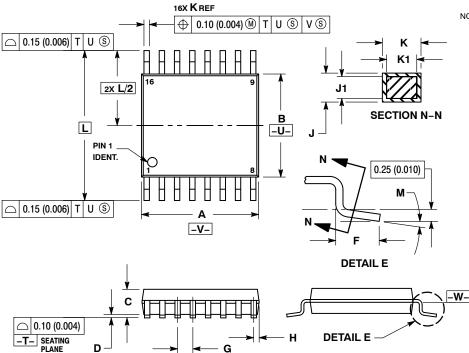
#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HC4046BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC4046BDR2G	SOIC-16 (Pb-Free)	2500 Units / Reel
NLV74HC4046ADR2G*	SOIC-16 (Pb-Free)	2500 Units / Reel
MC74HC4046BDTG	TSSOP-16 (Pb-Free)	96 Units / Rail
MC74HC4046BDTR2G	TSSOP-16 (Pb-Free)	2500 Units / Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

#### PACKAGE DIMENSIONS

#### TSSOP-16 CASE 948F **ISSUE B**



NOTES:

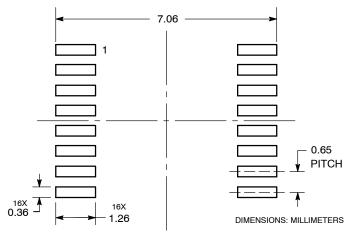
DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.
DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
DIMENSION K DOES NOT INCLUDE
DIMENSION K DOES NOT INCLUDE
DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08

DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

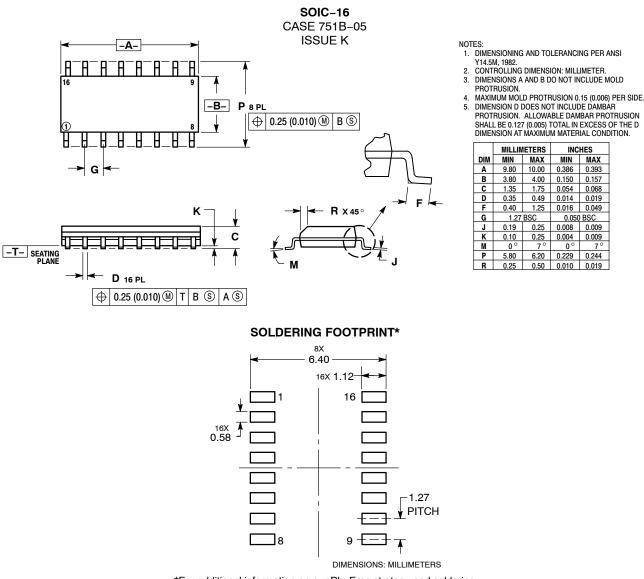
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
ĸ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L		BSC	0.252	BSC
М	0 °	8 °	0 °	8 °

**SOLDERING FOOTPRINT\*** 



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS



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